ABSTRACT OF THE DISCLOSURE

GROUP 3-5 COMPOUND SEMICONDUCTOR AND LIGHT EMITTING DIODE

A group 3-5 compound semiconductor comprising an interface of two layers having lattice mismatch, an intermediate layer having a film thickness of 25 nm or more and a quantum well layer, in this order. The compound semiconductor has high crystallinity and high quality, and suitably used for a light emitting diode.

(Figure 1)

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